

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	663	(438/458).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/10 07:40
L2	991	(438/455).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/10 07:41
L3	799	(438/459).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/10 07:41
L4	880	(438/404).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/10 07:41
L5	366	(438/406).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/10 07:41
L6	188	(438/407).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/10 07:41
L7	175	(438/423).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/10 07:41
L8	40	"438"/404,406,407,423,455,459, 458.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2"))) and (rare adj gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 07:42

L9	24	"438"/404,406,407,423,455,459, 458.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas)) and @ad<="20030226"	USPAT	OR	ON	2005/06/10 07:45
L10	8	"438"/404,406,407,423,455,459, 458.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas)) and @ad<="20030226" and delaminat\$4	USPAT	OR	ON	2005/06/10 07:46
L11	10	"438"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas)) and @ad<="20030226" and delaminat\$4	USPAT	OR	ON	2005/06/10 07:46
L12	10	"257"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas)) and @ad<="20030226" and delaminat\$4	USPAT	OR	ON	2005/06/10 07:45
S1	1	semiconductor and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) with (buried adj oxide) with (implant\$6 or dop\$6) with (hydrogen or ("H.sub.2")) with (rare adj gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 07:40
S2	1	"438"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) with (buried adj oxide) with (implant\$6 or dop\$6) with (hydrogen or ("H.sub.2")) with (rare adj gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 15:13
S3	0	"257"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) with (buried adj oxide) with (implant\$6 or dop\$6) with (hydrogen or ("H.sub.2")) with (rare adj gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 15:13

S4	3	"438"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) same (buried adj oxide) same (implant\$6 or dop\$6) with (hydrogen or ("H.sub.2")) same (rare adj gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 15:14
S5	87	"438"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and (implant\$6 or dop\$6) and (hydrogen or ("H.sub.2")) and (rare adj gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 15:14
S6	83	"438"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) with (hydrogen or ("H.sub.2")))) and (rare adj gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 15:15
S7	55	"438"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 07:42
S8	30	"438"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas))	USPAT	OR	ON	2005/06/06 15:17
S9	28	"438"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas)) and @ad<="20030226"	USPAT	OR	ON	2005/06/10 07:43
S10	19	"257"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas)) and @ad<="20030226"	USPAT	OR	ON	2005/06/06 15:18
S11	24	semiconductor and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas)) and @ad<="20030226"	USPAT	OR	ON	2005/06/07 06:16